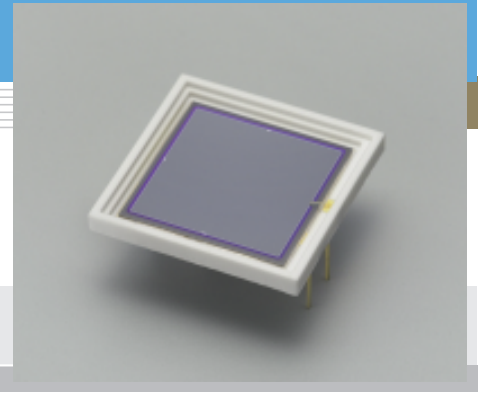


Si photodiode S6337-01

Large area photodiode for UV to IR, precision photometry



S6337-01 is a large area Si photodiode that features excellent spatial response uniformity over a wide range from UV to IR. S6337-01 will prove useful for precision photometry and as a standard detector for spectral response calibration.

Features

- Large active area: 18 × 18 mm
- Excellent uniformity even at wavelengths longer than 1000 nm
- High UV sensitivity

Applications

- Precision photometry
- Spectral response calibration
- Analytical equipment
- Trap detector

■ Absolute maximum ratings (Ta=25 °C)

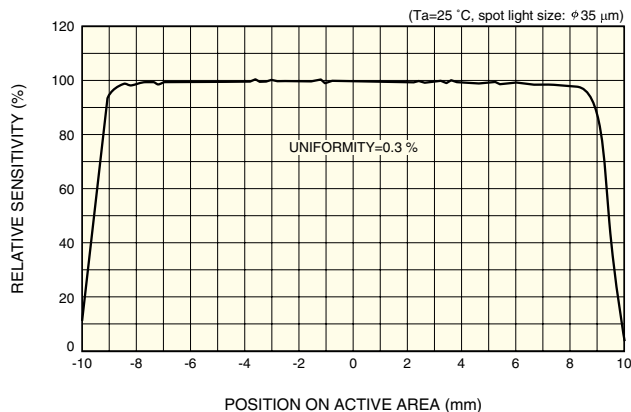
Parameter	Symbol	Value	Unit
Reverse voltage	VR Max.	5	V
Operating temperature	Topr	0 to +60	°C
Storage temperature	Tstg	0 to +80	°C

■ Electrical and optical characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ		-	190 to 1100	-	nm
Peak sensitivity wavelength	λ_p		-	960	-	nm
Photo sensitivity	S	$\lambda=\lambda_p$	-	530	-	mA/W
Short circuit current	Isc	100 lx, 2856 K	200	250	-	μ A
Dark current	ID	VR=10 mV	-	50	1000	pA
Rise time	tr	VR=0 V, RL=1 k Ω , λ =660 nm	-	7	-	μ s
Terminal capacitance	Ct	VR=0 V, f=10 kHz	-	3.5	-	nF
Shunt resistance	Rsh	VR=10 mV	10	200	-	M Ω
Uniformity *	U	Within 80 % of active area λ =190 to 1100 nm	-	-	0.5	%

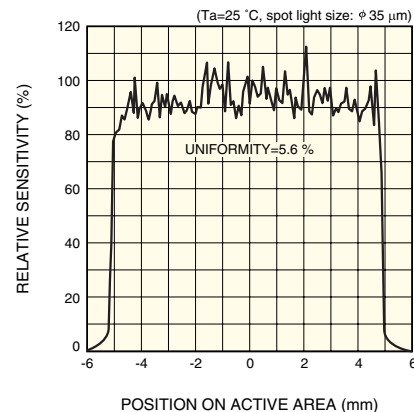
■ Sensitivity uniformity (typical example, λ =1100 nm)

S6337-01 (18 × 18 mm)



KSPDB0177EA

S1337-1010BQ (10 × 10 mm)



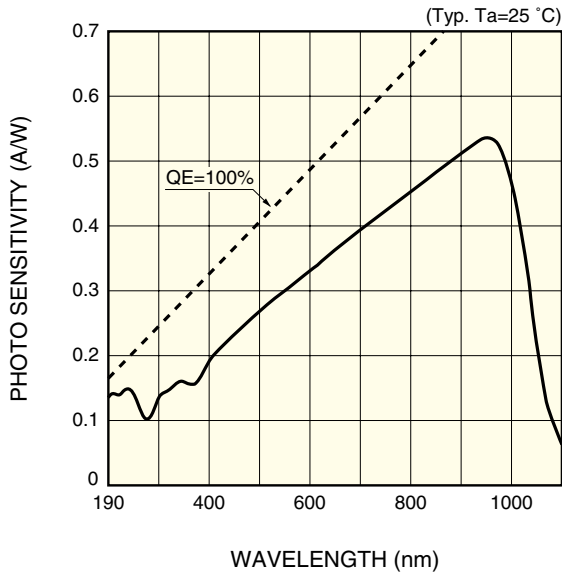
KSPDB0178EA

* Uniformity = Rs/Rm

Rs: Photo sensitivity at any point within 80 % of the active area

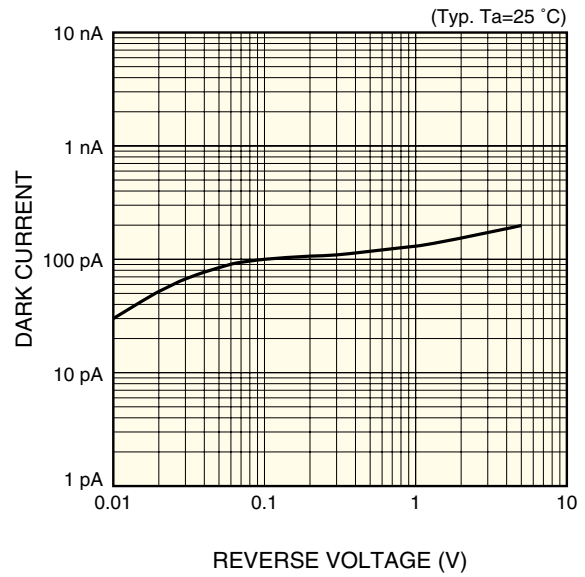
Rm: Averaged photo sensitivity within 80 % of the active area

■ Spectral response



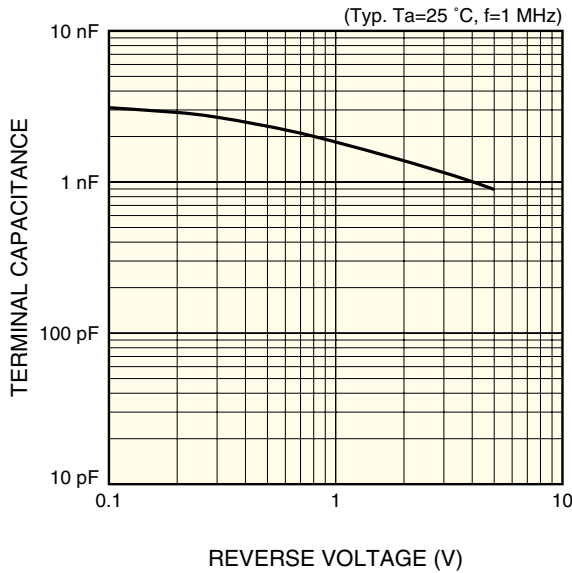
KSPDB0167EA

■ Dark current vs. reverse voltage



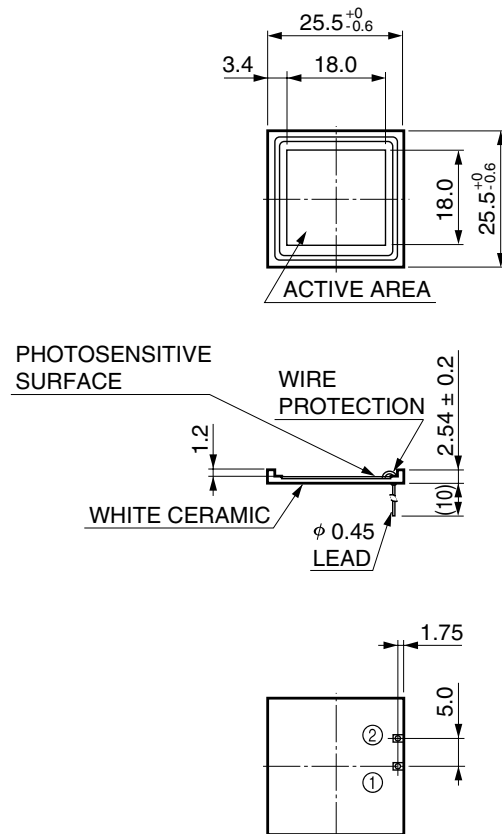
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■ Terminal capacitance vs. reverse voltage



KSPDB0165EA

■ Dimensional outline (unit: mm)



KSPDA0128EA

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Hamamatsu City, 435-8558 Japan, Telephone: (81) 053-434-3311, Fax: (81) 053-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 8, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741